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APPROVAL SHEET

Part No: **BF3H01G-NPT**

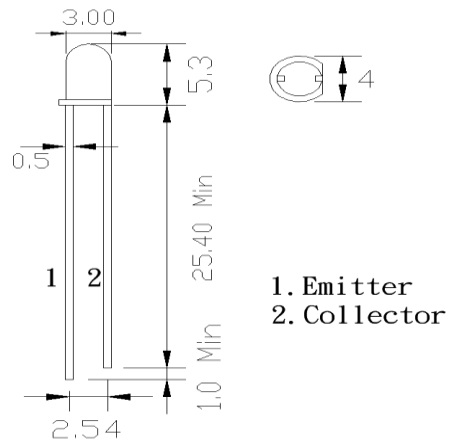
NOTE : Green Part

MAKER			CUSTOMER	
				
R&D	QA	Sales	Checked	Approved
				

Prepared	Checked	Approved
Rachel Lee	Sky Lin	Kenneth Wu

DESCRIPTION:

Device Type : BF3H01G-NPT
 Dice Material : Silicon
 Lens Color : Black
 Lens Dimension : 3 mm



All epoxy resin dimension are in millimeter
 tolerance is $\pm 0.2\text{mm}$

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Rating.	Unit
Power dissipation	P_d	75	mW
Operating Temperature	T_{opr}	-40 ~ +80	$^\circ\text{C}$
Storage Temperature	T_{str}	-40 ~ +100	$^\circ\text{C}$
Solder DIP (MAX. 5 seconds, 1.6mm from body) Temperature 260°C			

Electrical and Optical Characteristics at $T_a=25^\circ\text{C}$

Description	Symbol	Condition	Min.	Typ.	Max.	Unit
Range of Spectral Bandwid	W_p		400	-	1100	nm
Peak sensitive wavelength	W_p		-	940	-	nm
C-E breakdown voltage	BV_{CEO}	$I_C=100\mu\text{A}$	30	-	-	V
E-C breakdown voltage	BV_{ECO}	$I_E=100\mu\text{A}$	5	-	-	V
Collector dark current	I_{CEO}	$V_{CE}=20\text{V}$	-	-	100	nA
C-E saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{mA} / I_B=100\mu\text{A}$	-	-	0.2	V
Light Current	I_L	$E_e=1\text{mW}/\text{C mm}^2$ $V_{CE}=5\text{V}$	0.7	-	-	mA
Rise Time	t_r	$V_{CE}=5\text{V}$ $I_C=1\text{mA}$	-	15	-	μs
Fall Time	t_f	$R_L=1000\Omega$	-	15	-	

- Note:
- The lead should be formed up to 5mm from the body of device without forming stress.
 - Soldering shall be performed after lead forming.
 - All dimensions are in millimeters

LED LAMP Technical Data

Typical Optical-Electrical Characteristic Curves

